

Silicon NPN Power Transistors

2SD1577

DESCRIPTION

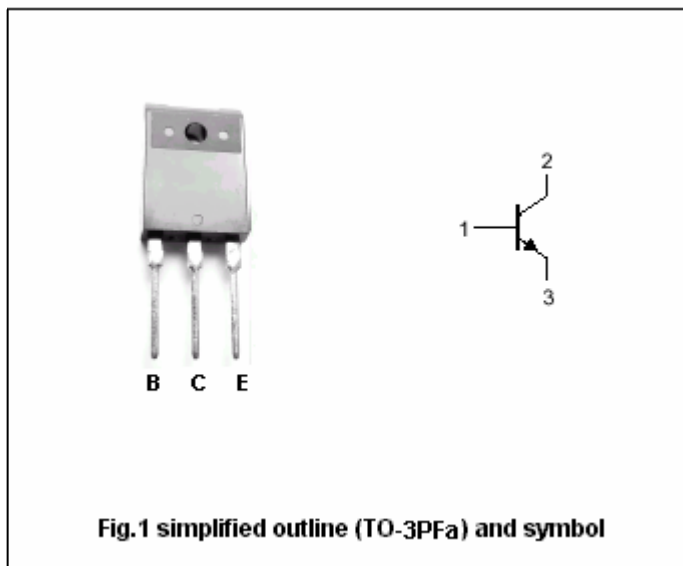
- With TO-3PFa package
- Wide area of safe operation
- High voltage, high speed

APPLICATIONS

- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		17	A
I_B	Base current		3.5	A
P_C	Collector power dissipation	$T_C=25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =2A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =2A			1.3	V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μ A
		V _{CB} =1500V; I _E =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μ A
h _{FE}	DC current gain	I _C =2A ; V _{CE} =10V	4		15	

Switching times

t _{stg}	Storage time	I _C =4A; L _B =10 μ H I _{Bend} =1.5A			11	μ s
t _f	Fall time				1	μ s

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PACKAGE OUTLINE

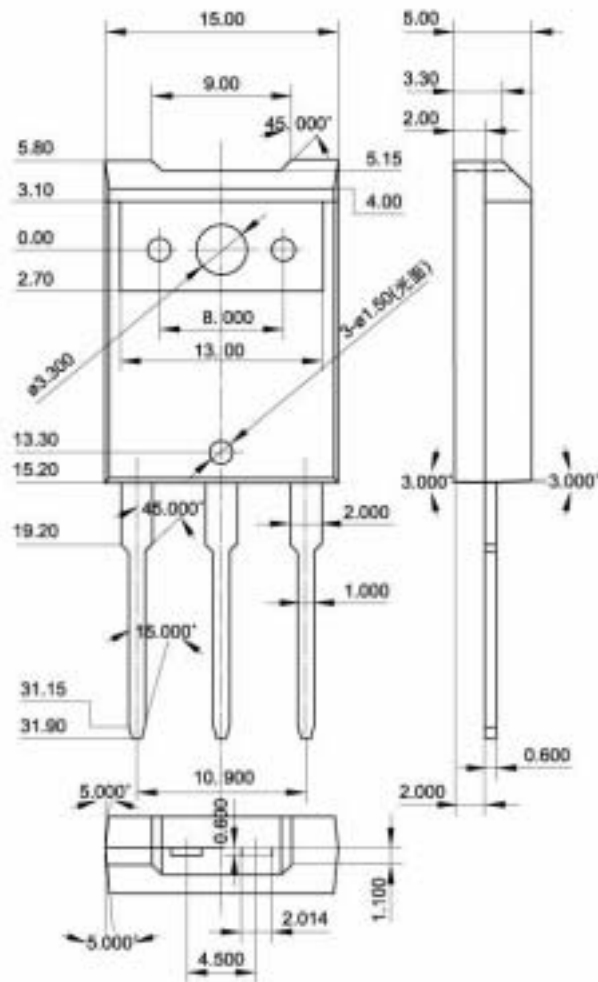


Fig.2 Outline dimensions (unindicated tolerance: ± 0.30 mm)